



Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12406-059US2	Application No. 10/625,118
Information Disclosure Statement by Applicant (Use several sheets if necessary)		Applicant Volker Haerle	
		Filing Date July 22, 2003	Group Art Unit Unknown <u>2824</u>

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation
							Yes No
	AL						
	AM						
	AN						
	AO						
	AP						

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
<u>BCO</u>	AQ	Sugano, Hikaru, "Semiconductor Laser Manufacturing Method", October 27, 1989, pp. 1-6
	AR	
	AS	
	AT	

Examiner Signature <u>Beth E. Owens</u>	Date Considered <u>2.17.04</u>
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Substitute Form PTO-1449 (MAY 2001) <i>OTTE</i> Information Disclosure Statement by Applicant AUG 25 2003 (37 CFR §1.98)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12406-059US2	Application No. 10/625,118
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	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
<i>Beo</i>	AQ	B. Henle, et. al., "In Situ Selective Area Etching and Movpe Regrowth Of GainsAs-InP ON InP Substrates," Int. Conf. On Indium Phosphide & Rel. Materials, U.S. NY, IEEE, Bd. CONF 4, S. pgs. 159-162
<i>✓</i>	AR	
	AS	
	AT	

Examiner Signature <i>Beth E. Owners</i>	Date Considered <i>2-17-04</i>
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		Filing Date Herewith	Group Art Unit Unknown <u>2824</u>

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
<u>BEO</u>	AA	4,415,404	11/15/1983	Riegl			
	AB	4,614,564	09/30/1986	Sheldon et al.			
	AC	4,816,098	03/28/1989	Davis et al.			
	AD	4,980,312	12/25/1990	Harris et al.			
	AE	5,268,069	12/07/1993	Chapple-Sokol et al.			
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	AG	5,668,038	09/16/1997	Huang et al.			
	AH	5,702,569	12/30/1997	Park et al.			
	AI	5,937,273	08/10/1999	Fujii et al.			
<u>BEO</u>	AJ	6,140,247	10/31/2000	Muraoka et al.			

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes No
<u>BEO</u>	AK	0746011	10/2001	EP			
<u>BEO</u>	AL	0681315	06/2000	EP			
<u>BEO</u>	AM	02-046407	02/1990	JP			
<u>BEO</u>	AN	07202317	08/1995	JP			
<u>BEO</u>	AO	01270287	10/1989	JP with English Abstract			X

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
<u>BEO</u>	AP	JP-61 210687 Patent Abstracts of Japan, Venoffentlichung, September 8, 1986
<u>BEO</u>	AQ	G.B., Burns, "Lo-Temperature Native Oxide Removal From Silicon Using Nitrogen Trifluoride Prior To Low-Temperaturé Silicon Epitaxy", Appl. Phys. Lett. 53 (15), October 1988 pp 1423-1425
<u>BEO</u>	AR	T. Aoyama et al. "Silicon Surface Cleaning Using Photo excited Fluorine Gas Diluted With Hydrogen", J. Electrochem. Soc. Vol. 140, No. 6, June 1993 pp 1704-1708
<u>BEO</u>	AS	K. Ozasa et al., "Deposition Of Thin Indium Oxide Film and Its Application To Selective Epitaxy For In Situ Processing" Thin Solid Films, BD. 246, NR. 1/02, 1994, S. 58-64, XP000453839
<u>BEO</u>	AT	J.P. Harbison et al., "Tungsten Patterning As A Technique For Selective Area III-V MBE Growth", J. Vac. Sci. Technol. B3(2) March/April 1995

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BeO	AU	JP 02-046407, Patent Abstracts of Japan, Veröffentlichung: February 2, 1990, Anmeldung: August 5, 1988
BeO	AV	S. Yoshida et al., "Selective-Area Epitaxy Of GaAs Using A New Mask Material For In Situ Processes", Inst. Phys. Conf. Ser. No. 129: Chapter 3, 1992, S-49-54, XP000366199
BeO	AW	P.J. Sullivan, et al., "Selective-Area Epitaxy For GaAs-on-InP Optoelectronic Integrated Circuits (OEICs)", Semiconductor Sci. & Technol. 8, No. 6, June 1993, pp 1179-1185
BeO	AX	Whidden T.K. et al.; "Catalyzed HF Vapor Etching Of Silicon Dioxide Für Micro-and Nanolithographic Masks", April 1995; J. Electrochem Soc., Vol. 142, No. 4, pp 1199-1204
BeO	AY	Torek K. et al.; "Reduced Pressure Etching Of Thermal Oxides In Anhydrous HF/Alcoholic Gas Mixtures"; April 1995; J. Electrochem Soc., Vol. 142, No. 4, pp 1322-1326
BeO	AZ	Wong M. et al., "Characterization Of Wafer Cleaning And Oxide And Oxide Etching Using Vapor-Phase Hydrogen Fluoride"; June 1991, J. Electrochem. Soc., Vol. 138, No. 6, pp 1799-1802

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